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TITLE: Method for manufacturing ~~capacitor~~ using atomic layer deposition

INVENTOR: LEE, J W

PATENT-ASSIGNEE: HYNIX SEMICONDUCTOR INC[HYNIN]

PRIORITY-DATA: 2000KR-0076627 (December 14, 2000)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
KR 384851 B	May 22, 2003	N/A	000	H01L 027/108
KR 2002046433 A	June 21, 2002	N/A	001	H01L 027/108

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
KR 384851B	N/A	2000KR-0076627	December 14, 2000
KR 384851B	Previous Publ.	KR2002046433	N/A
KR2002046433A	N/A	2000KR-0076627	December 14, 2000

INT-CL (IPC): H01L027/108

ABSTRACTED-PUB-NO: KR2002046433A

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BASIC-ABSTRACT:

NOVELTY - A fabrication method of a [REDACTED] is provided to improve quality and electrical properties by using an ALD(Atomic Layer Deposition) and an ammonia plasma treatment.

DETAILED DESCRIPTION - A lower electrode(21) and a [REDACTED] metal(22) are sequentially formed on a semiconductor substrate(20). A TaON dielectric film(23) is then formed on the [REDACTED] metal. A TiN upper electrode(24) is formed on the TaON dielectric film(23) by an [REDACTED] using TiCl4 as a source gas. The surface of the TaN upper electrode(24) is performed by NH3 plasma treatment so as to remove Cl radicals.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD MANUFACTURE [REDACTED] ATOMIC LAYER DEPOSIT

DERWENT-CLASS: L03 U11 U14

CPI-CODES: L03-G04A; L04-C11C2; L04-C12B; L04-C14A;

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